

# HAT2244WP

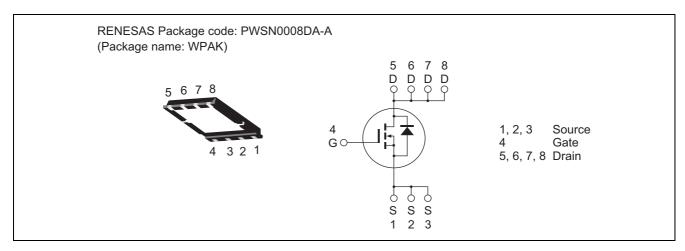
# Silicon N Channel Power MOS FET Power Switching

REJ03G1549-0400 Rev.4.00 Jun 13, 2007

### **Features**

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 10 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

### **Outline**



# **Absolute Maximum Ratings**

 $(\mathrm{Ta}=25^{\circ}\mathrm{C})$ 

Item	Symbol	Ratings	Unit	
Drain to source voltage	$V_{DSS}$	80	V	
Gate to source voltage	$V_{GSS}$	±20	V	
Drain current	I <sub>D</sub>	30	А	
Drain peak current	I <sub>D(pulse)</sub> Note1	120	А	
Body-drain diode reverse drain current	I <sub>DR</sub>	30	А	
Avalanche current	I <sub>AP</sub> Note 2	25	А	
Avalanche energy	E <sub>AR</sub> Note 2	83	mJ	
Channel dissipation	Pch Note3	25	W	
Channel to Case Thermal Impedance	θch-c Note3	5	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3.  $Tc = 25^{\circ}C$

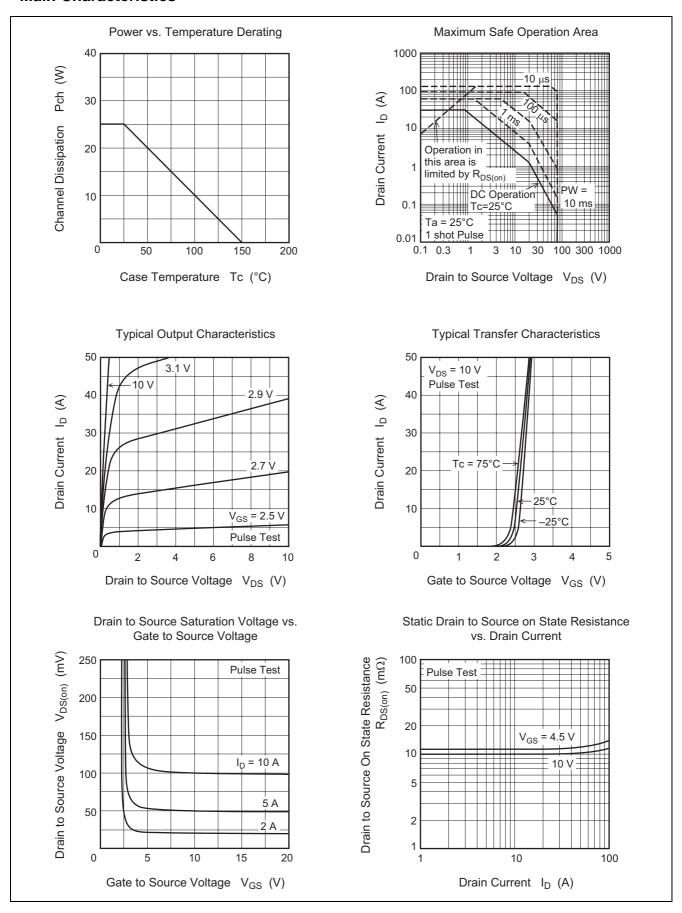
# **Electrical Characteristics**

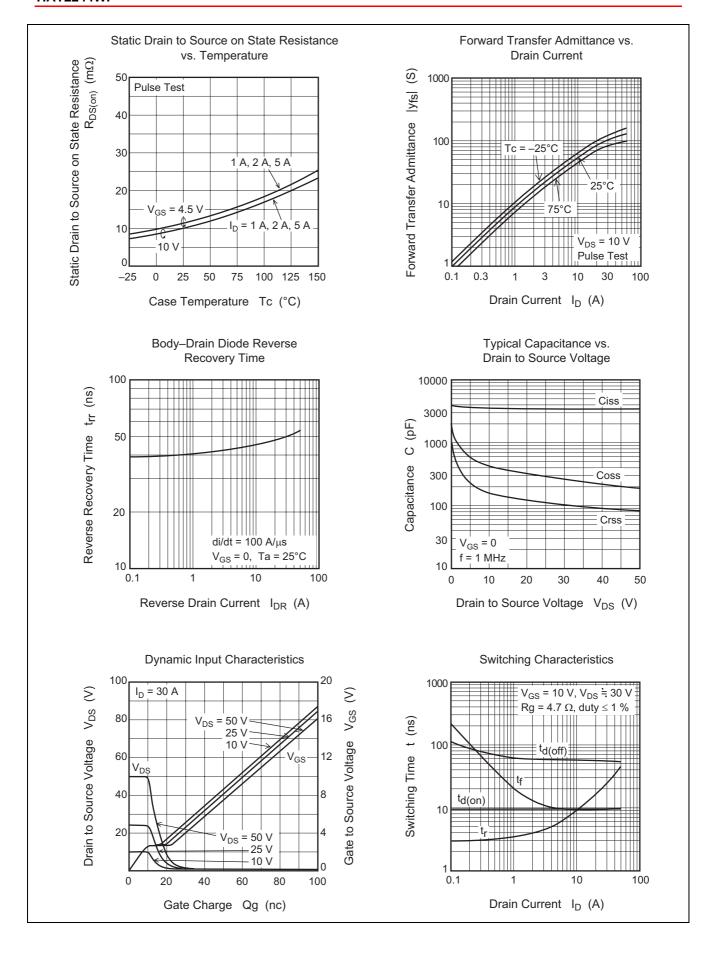
 $(Ta = 25^{\circ}C)$ 

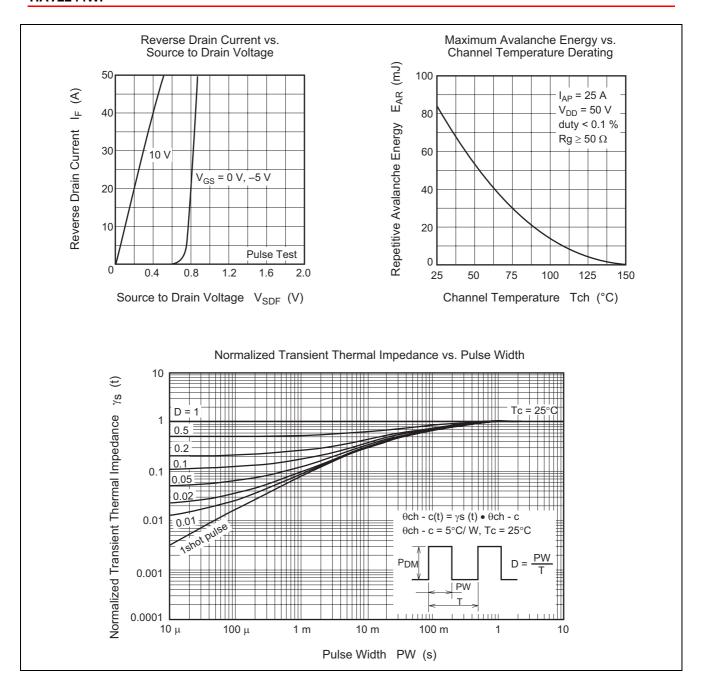
Symbol	Min	Тур	Max	Unit	Test Conditions
$V_{(BR)DSS}$	80	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
I <sub>GSS</sub>	_	_	± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
$V_{GS(off)}$	8.0	_	2.3	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
R <sub>DS(on)</sub>	_	10	12.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
R <sub>DS(on)</sub>	_	11.5	15.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
y <sub>fs</sub>	42	70	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Ciss	_	3520	_	pF	V <sub>DS</sub> = 10 V
Coss	_	410	_	pF	$V_{GS} = 0$
Crss	_	160	_	pF	f = 1 MHz
Rg	_	1.2	_	Ω	
Qg	_	60	_	nC	$V_{DD} = 25 \text{ V}$
Qgs	_	9.5	_	nC	V <sub>GS</sub> = 10 V
Qgd	_	9.0	_	nC	$I_D = 30 \text{ A}$
t <sub>d(on)</sub>	_	9.5	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$
t <sub>r</sub>	_	14.5	_	ns	$V_{DD} \cong 30 \text{ V}$
t <sub>d(off)</sub>	_	56	_	ns	$R_L = 2 \Omega$
t <sub>f</sub>	_	9.5	_	ns	$Rg = 4.7 \Omega$
$V_{DF}$	_	0.83	1.08	V	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 Note4
t <sub>rr</sub>	_	50	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$
	V(BR)DSS  IGSS  IDSS  VGS(off)  RDS(on)  RDS(on)  IVfs  Ciss  Coss  Crss  Rg  Qg  Qgs  Qgd  td(on)  tr  td(off)  tf  VDF	V(BR)DSS         80           IGSS         —           VGS(off)         0.8           RDS(on)         —           RDS(on)         —           Iyfs         42           Ciss         —           Coss         —           Crss         —           Rg         —           Qg         —           Qgd         —           td(on)         —           tf         —           VDF         —	V(BR)DSS         80         —           IGSS         —         —           VGS(off)         0.8         —           RDS(on)         —         10           RDS(on)         —         11.5           Jyfs         42         70           Ciss         —         3520           Coss         —         410           Crss         —         160           Rg         —         1.2           Qg         —         60           Qgs         —         9.5           Qgd         —         9.0           td(on)         —         9.5           tf         —         14.5           td(off)         —         56           tf         —         9.5           VDF         —         0.83	V(BR)DSS         80         —         —           IGSS         —         —         ± 0.5           IDSS         —         —         1           VGS(off)         0.8         —         2.3           RDS(on)         —         10         12.5           RDS(on)         —         11.5         15.5           JYfs         42         70         —           Ciss         —         3520         —           Coss         —         410         —           Crss         —         160         —           Rg         —         1.2         —           Qg         —         60         —           Qgs         —         9.5         —           Qgd         —         9.0         —           td(on)         —         9.5         —           tr         —         14.5         —           tf         —         9.5         —           VDF         —         0.83         1.08	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

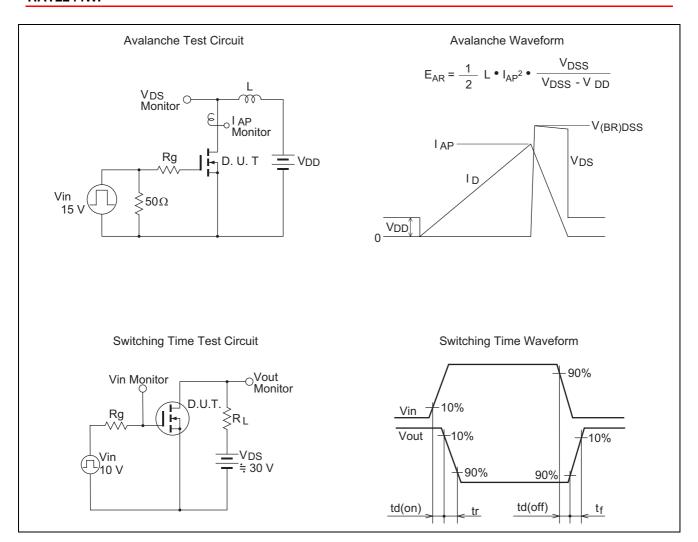
Notes: 4. Pulse test

### **Main Characteristics**

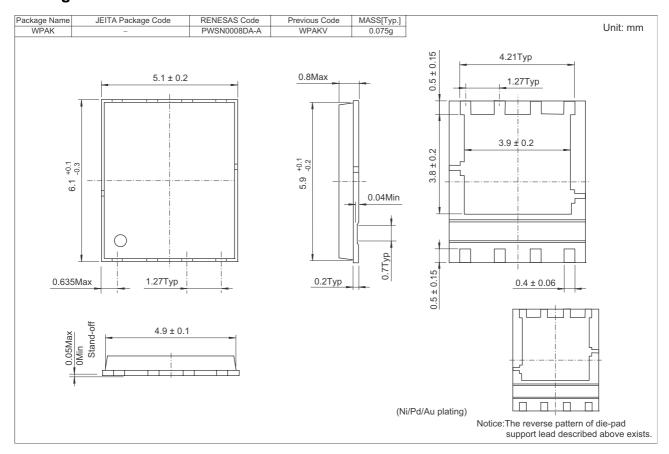








# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2244WP-EL-E	2500pcs	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect to the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510